

ABSTRACT

Disclosed are a row decoder in a flash memory and erasing method in a flash memory cell using the same. The row decoder comprises a PMOS transistor having a gate electrode for receiving a first input signal as an input and connected between a first power supply terminal and a first node, a first NMOS transistor having a gate electrode for receiving the first input signal as an input and connected between the first node and a second node, a second NMOS transistor having a gate electrode for receiving the second input signal as an input and connected between the second node and a ground terminal, and a switching means having a gate electrode for receiving the third input signal as an input and connected between the second node and a second power supply terminal, wherein the first node is connected to word lines. Therefore, the present invention can prevent an insulating break phenomenon of the ONO insulating film that may happen during an erasing operation such as cycling, etc. *deleted.*

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